NSN 5962-01-262-3637

Memory Microcircuit - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5962-01-262-3637

Body Length:

Between 0.442 inches and 0.460 inches

Body Width:

Between 0.442 inches and 0.460 inches

Body Height:

Between 0.060 inches and 0.100 inches

Maximum Power Dissipation Rating:

1.02 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Programmed and edge triggered and monolithic and asynchronous

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

14 input

Case Outline Source And Designator:

C-4 mil-m-38510

Current Rating Per Characteristic:

185.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

Registered prom

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Capitance Rating Per Characteristic:

10.00 input picofarads and 13.00 output picofarads

Time Rating Per Chacteristic:

45.00 nanoseconds af output megawatts

Memory Device Type:

Prom

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 leadless

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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